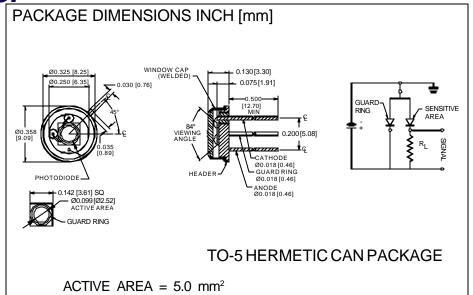
PHOTONIC DETECTORS INC.

1.06 Micron, High Speed Silicon Photodiode Type PDI-M301





FEATURES

- .45 A/W @1060 nm
- 11 ns response time
- Low noise

DESCRIPTION

The **PDI-M301** is a high speed photodiode, processed on high resistivity P type silicon. Guard ring construction for enhanced 1060 nm response and 28 Mhz bandwidth. Packaged in a 3 leaded hermetic TO-5 hermetic package. Ideal for Nd YAG laser.

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

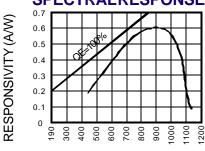
SYMBOL	PARAMETER	MIN	MAX	UNITS	
$V_{\mathtt{BR}}$	Reverse Voltage		75	V	
T_{STG}	Storage Temperature	-55	+125	⊙C	
T _O	Operating Temperature Range	-40	+100	⊙C	
T _s	Soldering Temperature*		+260	∘C	
١ _L	Light Current		500	mA	

^{*1/16} inch from case for 3 secs max

APPLICATIONS

- YAG laser detection
- High speed IR sensor
- Optical pyrometer sensor

SPECTRALRESPONSE



WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l _{sc}	Short Circuit Current	H = 100 fc, 2850 K	40	60		μΑ
I _D	Dark Current	$H = 0, V_R = 200 V$		9	16	nA
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$		100		MΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-10		%/℃
C_J	Junction Capacitance	$H = 0, V_R = 200 V^{**}$		2.8	3.0	pF
λrange	Spectral Application Range	Spot Scan	400		1150	nm
λр	Spectral Response - Peak	Spot Scan		900		nm
V _{BR}	Breakdown Voltage	Ι=1 μΑ	250	400		V
NEP	Noise Equivalent Power	V _R = 10 V @ 900 nm		1.5x10 ⁻¹²		W/ √Hz
tr	Response Time	$RL = 1 K\Omega V_R = 200 V$		11		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f=1 MHz [FORM NO. 100-PDI-M301 REV C]